

SMD Type

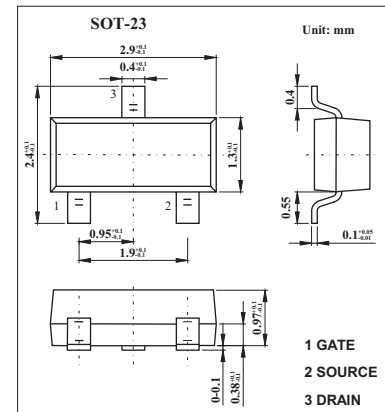
MOSFET

MOS Fied Effect Transistor

2SJ203

■ Features

- Directly driven by lcs having a 3V poer supply.
- Not necessary to consider driving current thanks to high input impedance.
- Possible to reduce the number of parts by omitting the bias resistor.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage V _{GS} =0	V _{DSS}	-16	V
Gate to source voltage V _{DS} =0	V _{GSS}	±7	V
Drain current (DC)	I _D	±200	mA
Drain current(pulse) *	I _D	±400	mA
Power dissipation	P _D	200	m W
Channel temperature	T _{ch}	-55 to 80	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 ms; d ≤ 50%.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	I _{DSS}	V _{DS} =-16V, V _{GS} =0			-10	μ A
Gate leakage current	I _{GSS}	V _{GS} =±3V, V _{DS} =0			±10	μ A
Gate cut-off voltage	V _{GS(off)}	V _{DS} =-3V, I _D =-1 μ A	-1.0	-1.6	-2.2	V
Forward transfer admittance	Y _{fs}	V _{DS} =-3V, I _D =-10mA	20	48		ms
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =-2.5V, I _D =-1mA		15	23	Ω
		V _{GS} =-4.0V, I _D =-1mA		7	10	Ω
Input capacitance	C _{iss}	V _{DS} =-3.0V, V _{GS} =0, f=1MHZ		28		pF
Output capacitance	C _{oss}			32		pF
Reverse transfer capacitance	C _{rss}			6		pF
Turn-on delay time	t _{d(on)}	V _{GS(on)} =-3V, R _G =10 Ω, V _{DS} =-3.0V, I _D =-10mA R _L =300 Ω		180		ns
Rise time	t _r			420		ns
Turn-off delay time	t _{d(off)}			100		ns
Fall time	t _f			200		ns

■ Marking

Marking	H14
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